



FZT692B

#### 70V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

#### **Features**

- BVcEo > 70V
- BVcBo > 70V
- I<sub>C</sub> = 2A High Continuous Current
- hFE > 400 for High Gain @ 0.5A
- Complementary PNP Type: FZT792A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

## **Mechanical Data**

- Package: SOT223
- Package Material: Molded Plastic, "Green" Molding Compound;
  UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

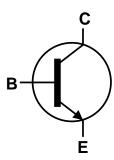
#### **Applications**

- Darlington replacements
- Relay and solenoid drivers
- DC-DC converters

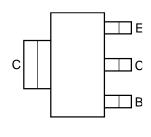
SOT223 (Type DN)



Top View



Device Symbol



Top View Pin-Out

## **Ordering Information** (Note 4)

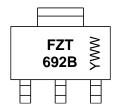
Part Number	Compliance	Package	Marking	Reel Size	Tape Width	Packing	
I art Namber	Compliance	1 ackage	Marking	(inches)	(mm)	Qty.	Carrier
FZT692BTA	Standard	SOT223 (Type DN)	FZT692B	7	12	1,000	Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**

SOT223 (Type DN)



FZT 692B = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 2 = 2022) WW or  $\overline{W}W$  = Week Code (01 to 53)



# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	70	V
Collector-Emitter Voltage	VCEO	70	V
Emitter-Base Voltage	VEBO	7	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	Ісм	5	Α

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	D <sub>=</sub>	2.0	W	
Power Dissipation	(Note 7)	P <sub>D</sub>	1.6		
	(Note 8)		1.2	1	
	(Note 5)		41.7		
Thermal Peciatones, Junction to Ambient	(Note 6)	] _	62.5		
Thermal Resistance, Junction to Ambient	(Note 7) R <sub>θ</sub> JA		78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		Rejl	12.9		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

# ESD Ratings (Note 10)

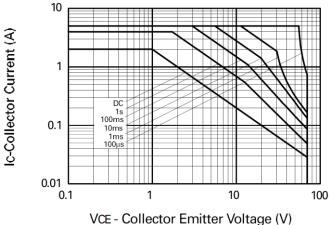
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

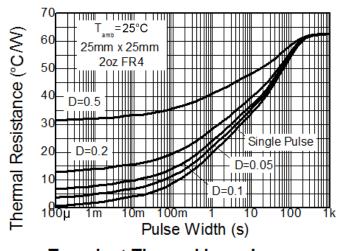
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a conditions whilst operating in a steady-state.
   Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
   Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
   Same as Note 5, except the device is mounted on minimum recommended pad layout.
   Thermal resistance from junction to solder-point (at the end of the collector lead).
   Refer to JEDEC specification JESD22-A114 and JESD22-A115.



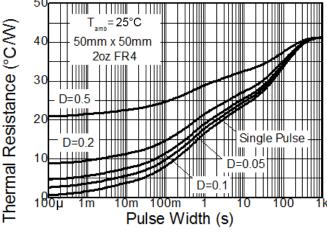
## Thermal Characteristics and Derating Information



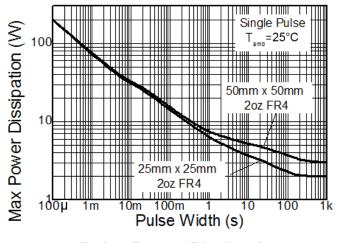
## Safe Operating Area



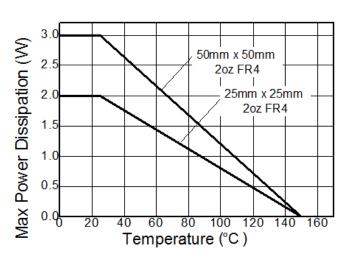
Transient Thermal Impedance



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



**Derating Curve** 



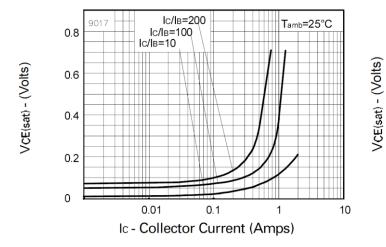
# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

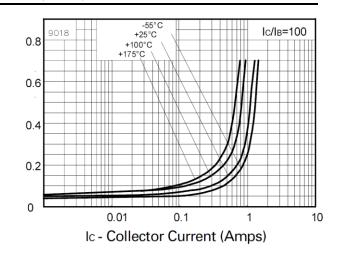
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	70	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BVceo	70	_	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	ВУЕВО	7	_	_	V	I <sub>E</sub> = 100μA
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_	_	50	nA	V <sub>CB</sub> = 55V
Collector-Emitter Cut-Off Current	Ices	_	_	50	nA	V <sub>CE</sub> = 55V
Emitter Cut-Off Current	IEBO	_	_	20	nA	V <sub>EB</sub> = 6V
DC Current Gain (Note 11)	h <sub>FE</sub>	500 400 150	_ _ _	_ _ _	_	Ic = 100mA, VcE = 2V Ic = 500mA, VcE = 2V Ic = 1A, VcE = 2V
Collector-Emitter Saturation Voltage (Note 11)	VCE(sat)	_ _ _	_ _ _	150 500 500	mV	I <sub>C</sub> = 0.1A, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 1A, I <sub>B</sub> = 10mA I <sub>C</sub> = 2A, I <sub>B</sub> = 200mA
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	_	_	0.9	V	Ic = 1A, I <sub>B</sub> = 10mA
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	_	_	0.9	V	Ic = 1A, VcE = 2V
Input Capacitance	Cibo	_	200	_	pF	V <sub>EB</sub> = 0.5V, f = 1MHz
Output Capacitance	Cobo	_	12	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Current Gain-Bandwidth Product	f⊤	150	_	_	MHz	V <sub>CE</sub> = 5V, I <sub>C</sub> = 50mA, f = 50MHz
Turn-On Time	ton	_	46	_	ns	Vcc = 10V, Ic = 500mA
Turn-Off Time	t <sub>off</sub>	_	1440	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

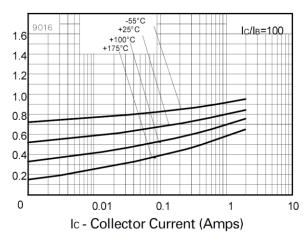




### VCE(sat) v IC

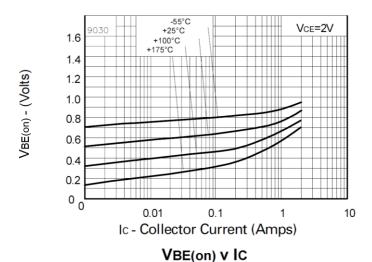
+100°C Vce=2V 1.6 +25°C 1.5K -55°C 1.4 hFE - Normalised Gain VBE(sat) - (Volts) 1.2 1.0 0.8 0.6 0.4 0.2 0 0 0.01 0.1 10

VCE(sat) v IC



Ic - Collector Current (Amps)

hFE v IC



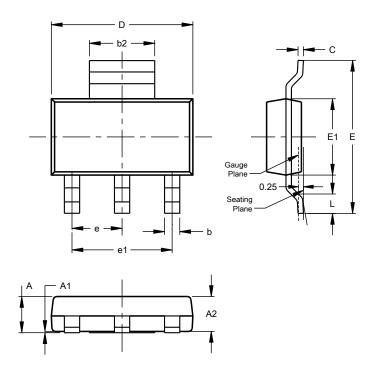
VBE(sat) v IC



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

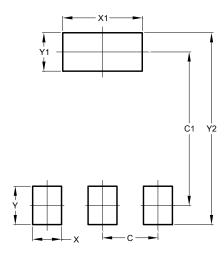


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
V2	8 00



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